

# Zhongliang Qiao

## List of Publications by Year in descending order

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24  
papers

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1163117

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docs citations

24  
times ranked

140  
citing authors

#	ARTICLE	IF	CITATIONS
1	Mode-locked operation characteristics of a monolithic integrated two-section InGaAs/GaAs double quantum wells laser with asymmetric waveguide. Optics and Laser Technology, 2022, 147, 107702.	4.6	1
2	Modal gain characteristics of a two-section InGaAs/GaAs double quantum well passively mode-locked laser with asymmetric waveguide. Scientific Reports, 2022, 12, 5010.	3.3	1
3	Research on Silicon-Substrate-Integrated Widely Tunable, Narrow Linewidth External Cavity Lasers. Crystals, 2022, 12, 674.	2.2	3
4	Wafer-Scale Demonstration of Low-Loss ( $\sim 0.43$ dB/cm), High-Bandwidth ( $> 38$ GHz), Silicon Photonics Platform Operating at the C-Band. IEEE Photonics Journal, 2022, 14, 1-9.	2.0	8
5	Research on Narrow Linewidth External Cavity Semiconductor Lasers. Crystals, 2022, 12, 956.	2.2	8
6	Stable Mode-Locked Operation With High Temperature Characteristics of a Two-Section InGaAs/GaAs Double Quantum Wells Laser. IEEE Access, 2021, 9, 16608-16614.	4.2	1
7	Compact, Hybrid III-V/Silicon Vernier Laser Diode Operating From 1955–1992 nm. IEEE Photonics Journal, 2021, 13, 1-5.	2.0	1
8	All-Solid-State DUV Light Source by Quadrupling of an Acousto-Optically Q-Switched Nd:YVO <sub>4</sub> Laser. IEEE Access, 2021, 9, 165989-165995.	4.2	0
9	Direct parameter extraction method for InP heterojunction bipolar transistors based on the combination of T- and ĩ€-models up to 110 GHz. Semiconductor Science and Technology, 2020, 35, 025001.	2.0	5
10	Temperature-dependent phase noise properties of a two-section GaSb-based mode-locked laser emitting at 2 ĩ¼m. Applied Physics Letters, 2020, 117, 141103.	3.3	2
11	Analysis of Compact Silicon Photonic Hybrid Ring External Cavity (SHREC) Wavelength-Tunable Laser Diodes Operating From 1881–1947 nm. IEEE Journal of Quantum Electronics, 2020, 56, 1-11.	1.9	4
12	1 Ā– N (N = 2, 8) Silicon Selector Switch for Prospective Technologies at the 2 ĩ¼m Waveband. IEEE Photonics Technology Letters, 2020, 32, 1127-1130.	2.5	12
13	Imaging the defect distribution in 2D hexagonal boron nitride by tracing photogenerated electron dynamics. Journal Physics D: Applied Physics, 2020, 53, 405106.	2.8	5
14	Compact silicon photonic hybrid ring external cavity (SHREC)/InGaSb-AlGaAsSb wavelength-tunable laser diode operating from 1881-1947–...nm. Optics Express, 2020, 28, 5134.	3.4	17
15	Sub-kHz linewidth, hybrid III-V/silicon wavelength-tunable laser diode operating at the application-rich 1647-1690–...nm. Optics Express, 2020, 28, 25215.	3.4	14
16	High temperature characteristics of a 2 ĩ¼m InGaSb/AlGaAsSb passively mode-locked quantum well laser. Applied Physics Letters, 2019, 114, .	3.3	8
17	The design of 1 Ā– 2 MMI at the MIR wavelength of 2 ĩ¼m. , 2019, , .		1
18	High-performance 1.06- ĩ¼m InGaAs/GaAs double-quantum-well semiconductor lasers with asymmetric heterostructure layers. Semiconductor Science and Technology, 2019, 34, 055013.	2.0	9

#	ARTICLE	IF	CITATIONS
19	Silicon Nitride Waveguiding for Prospective Technologies at the 2 $\mu\text{m}$ Waveband. , 2019, , .		0
20	Two-mode multiplexer based on the multilayer Si-SiN platform for 2 $\mu\text{m}$ waveband. , 2019, , .		0
21	Investigation of regime switching from mode locking to Q-switching in a 2 $\mu\text{m}$ InGaSb/AlGaAsSb quantum well laser. Optics Express, 2018, 26, 8289.	3.4	13
22	Temperature- and current-dependent spontaneous emission study on 2 $\mu\text{m}$ InGaSb/AlGaAsSb quantum well lasers. Japanese Journal of Applied Physics, 2017, 56, 050310.	1.5	4
23	Modal gain characteristics of a 2 $\mu\text{m}$ InGaSb/AlGaAsSb passively mode-locked quantum well laser. Applied Physics Letters, 2017, 111, .	3.3	20
24	Design and Analysis of 2 $\mu\text{m}$ InGaSb/GaSb Quantum Well Lasers Integrated Onto Silicon-on-Insulator (SOI) Waveguide Circuits Through an Al <sub>2</sub> O <sub>3</sub> Bonding Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2016, 22, 16-22.	2.9	13